

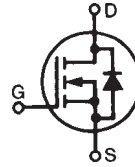
**Polar™**  
**Power MOSFET**

**IXTP18N60PM**

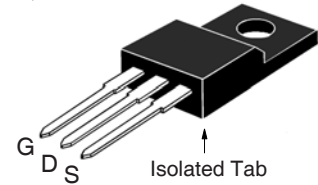
$V_{DSS} = 600V$   
 $I_{D25} = 9A$   
 $R_{DS(on)} \leq 420m\Omega$

**(Electrically Isolated Tab)**

N-Channel Enhancement Mode  
Avalanche Rated



**OVERMOLDED  
(IXTP...M) OUTLINE**



G = Gate      D = Drain  
S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	600	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	9	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	54	A
$I_A$	$T_C = 25^\circ C$	18	A
$E_{AS}$	$T_C = 25^\circ C$	1	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_D$	$T_C = 25^\circ C$	90	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062in.) from Case for 10s	300	$^\circ C$
$T_{sold}$	Plastic Body for 10 Seconds	260	$^\circ C$
$M_d$	Mounting Torque	1.13 / 10	Nm/lb.in.
<b>Weight</b>		2.5	g

**Features**

- Plastic Overmolded Tab for Electrical Isolation
- International Standard Package
- Low  $R_{DS(on)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

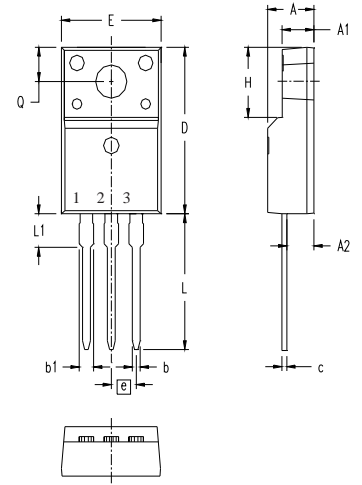
Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$			25 $\mu A$
	$T_J = 125^\circ C$			250 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 9A$ , Note 1			420 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 9\text{A}$ , Note 1	9	16	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		2500	pF
$C_{oss}$			280	pF
$C_{rss}$			23	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 9\text{A}$ $R_G = 5\Omega$ (External)		21	ns
$t_r$			22	ns
$t_{d(off)}$			62	ns
$t_f$			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 9\text{A}$		50	nC
$Q_{gs}$			15	nC
$Q_{gd}$			18	nC
$R_{thJC}$				1.39 $^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			18 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			54 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		500	ns

### OVERMOLDED TO-220



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\varnothing P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

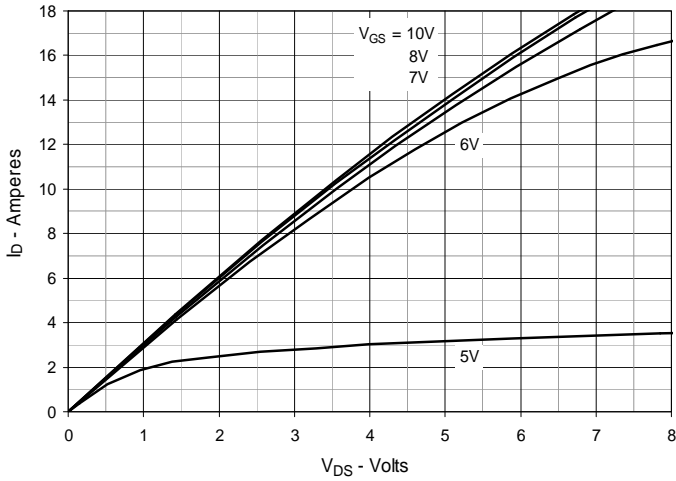
Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

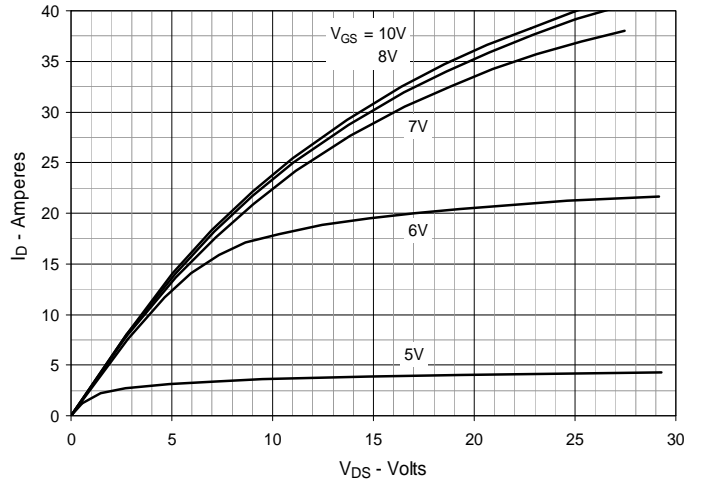
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

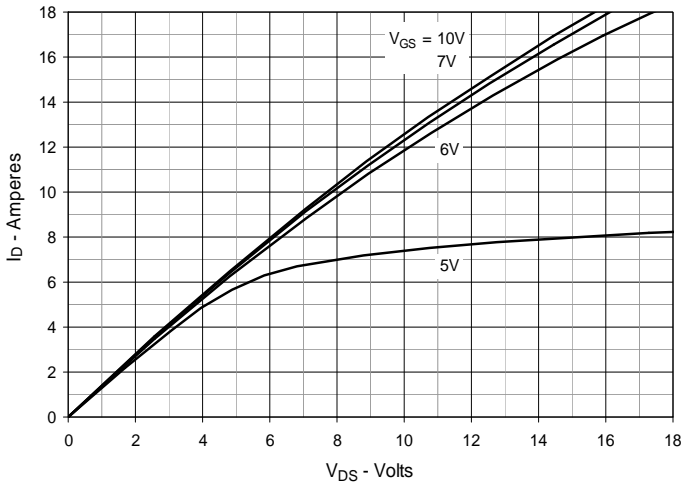
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



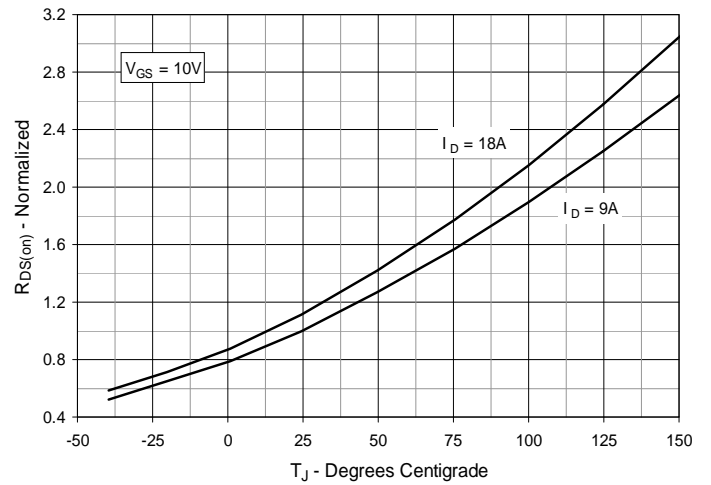
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



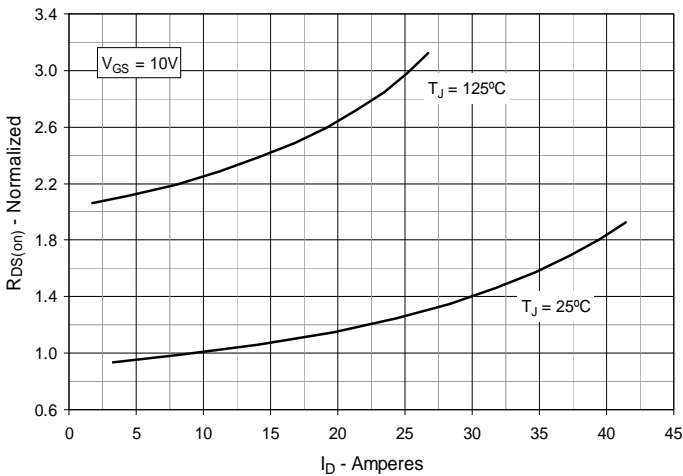
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



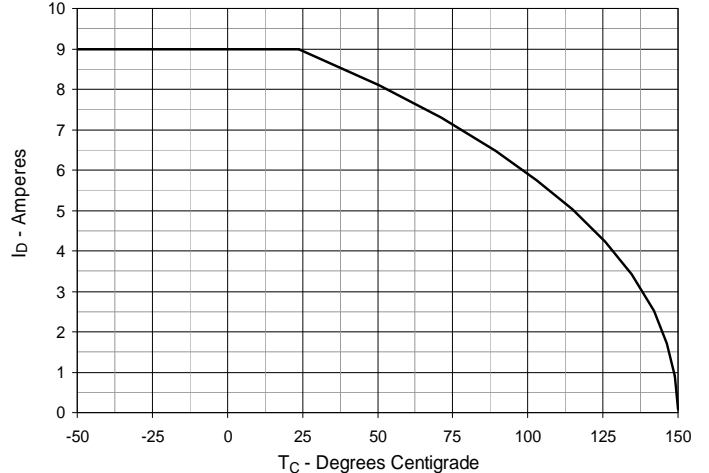
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 9\text{A}$  Value vs. Junction Temperature**



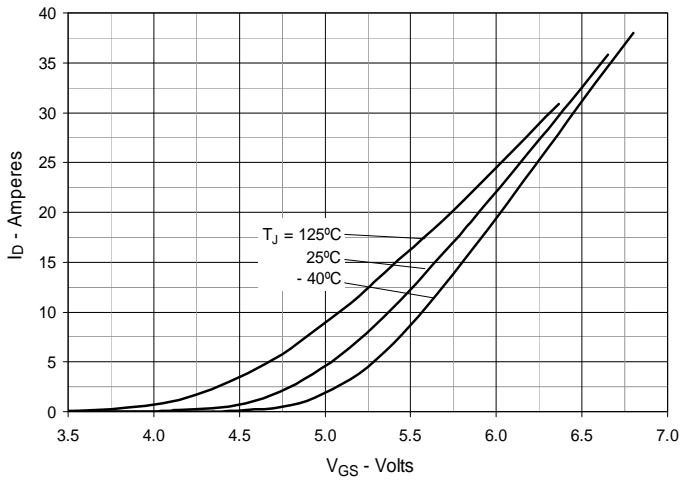
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 9\text{A}$  Value vs. Drain Current**



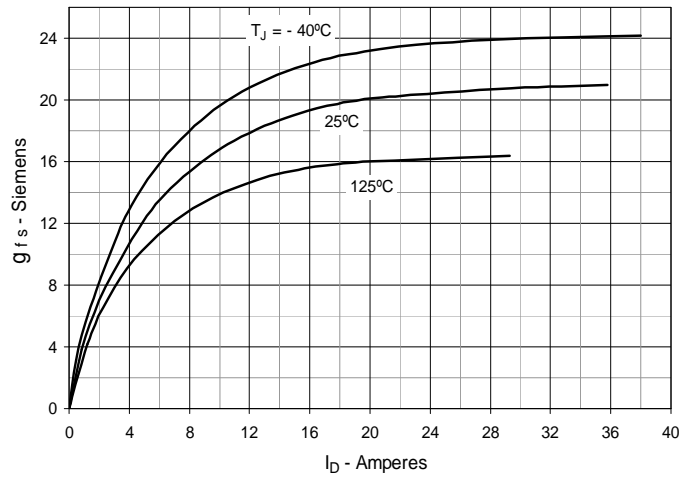
**Fig. 6. Maximum Drain Current vs. Case Temperature**



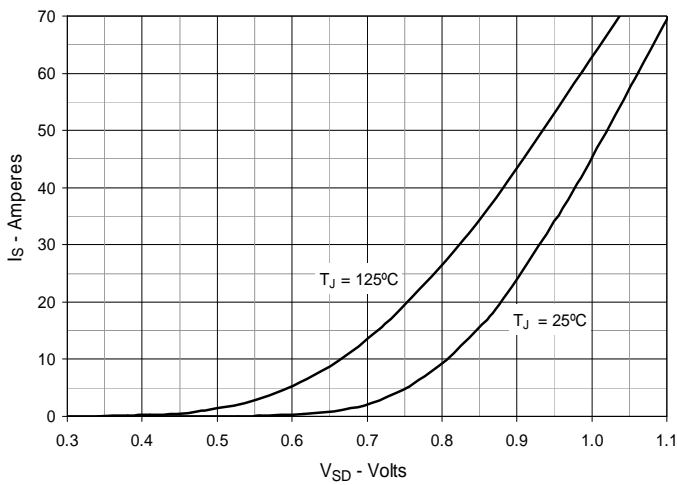
**Fig. 7. Input Admittance**



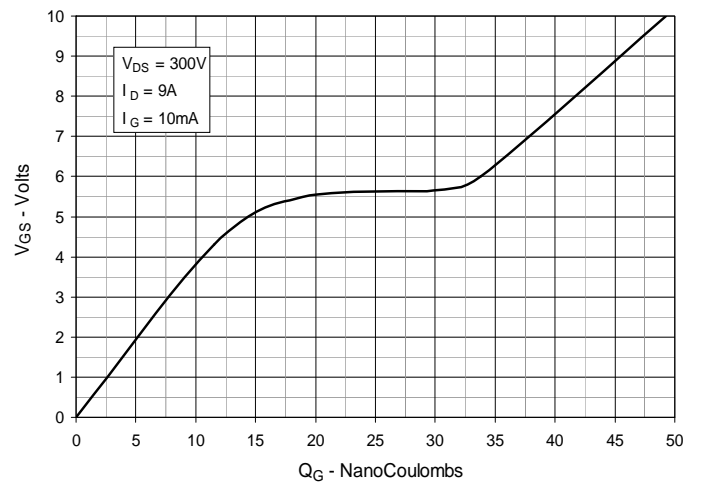
**Fig. 8. Transconductance**



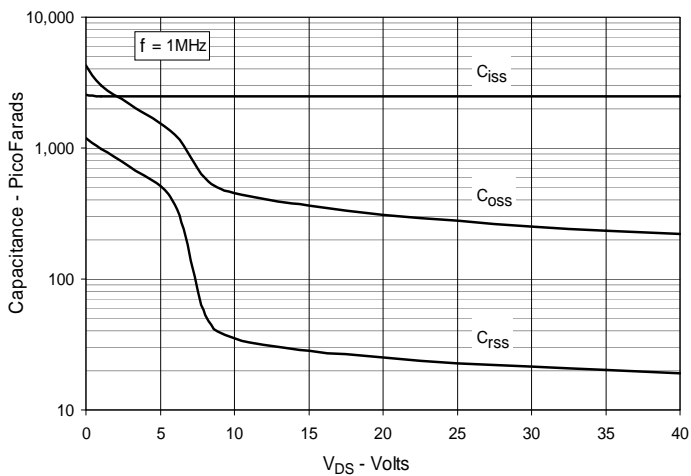
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

